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B<sup>1</sup>

a first insulating film formed on said first conductor;

a second conductor including a first plug and a second plug formed on said first conductor through said first insulating film;

a third conductor including a first wire formed on said first insulating film and the first plug and a second wire formed on an extension line of the first wire on said first insulating film and the second plug; and

a second insulating film formed on said third conductor and over said first insulating film, said second insulating film including a thin area over said second conductor for guiding a laser beam.

2. (Twice Amended) The semiconductor device of claim 1, wherein:

said second conductor includes a third plug and a fourth plug formed on said first conductor through said first insulating film; and

said third conductor includes a third wire formed parallel with the first wire on said first insulating film and the third plug and a fourth wire formed on an extension line of the third wire on said first insulating film and the fourth plug.

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5. (Twice Amended) The semiconductor device of claim 2, wherein:

said second conductor includes a fifth plug lined up on a first straight line with the first plug and the third plug on said first conductor through said first insulating film and a sixth plug lined up on a second straight line with the second plug and the fourth plug on said first conductor through said first insulating film.

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31. (Amended) The semiconductor device of claim 30, further comprising:  
a second lower wire formed on an extension line of said first lower wire on said first insulating film beneath said second insulating film;  
a second conductor formed through said second insulating film below the thin area including a third portion formed on said second lower wire made of a same material as the first portion and a fourth portion formed on the third portion made of a same material as the second portion; and  
a second upper wire formed parallel with said second lower wire on said second insulating film and said second conductor beneath said third insulating film.

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34. (Amended) The semiconductor device of claim 33, further comprising:  
a second conductor formed on said semiconductor substrate through said first insulating film below the thin area; and  
a second upper wire formed on an extension line of said first upper wire on said first insulating film and said second conductor beneath said second insulating film.

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36. (Amended) A semiconductor device comprising:  
a semiconductor substrate;  
a first insulating film formed on said semiconductor substrate;  
first conductors formed on said semiconductor substrate through said first insulating film;

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first upper wires formed on said first insulating film and said first conductors alternated on two parallel rows such that ends of said first upper wires on one of the parallel rows oppose ends of said first upper wires on the other of the parallel rows; and a second insulating film formed on said first upper wires and over said first insulating film, said second insulating film including a thin area over said first conductors for guiding a laser beam.

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38. (Amended) A semiconductor device comprising:  
a first insulating film;  
first lower wires formed on said first insulating film alternated on two parallel rows such that ends of said first lower wires on one of the parallel rows oppose ends of said first lower wires on the other of the parallel rows;  
a second insulating film formed on said first lower wires;  
first conductors formed on said first lower wires through said second insulating film;  
first upper wires formed parallel with said first lower wires on said second insulating film and said first conductors; and  
a third insulating film formed on said first upper wires and over said second insulating film, said third insulating film including a thin area over said first conductors for guiding a laser beam.

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42. (Amended) The semiconductor device of claim 41, further comprising:  
a second lower wire formed parallel with said first lower wire on said first insulating film beneath said second insulating film;  
a third conductor formed on said second lower wire below the thin area through said second insulating film;  
a fourth conductor formed on said second lower wire below the thin area through said second insulating film;  
a third upper wire formed on an extension line of said first upper wire on said second insulating film and said third conductor beneath said third insulating film; and  
a fourth upper wire formed on an extension line of said second upper wire on said second insulating film and said fourth conductor beneath said third insulating film.

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44. (Amended) The semiconductor device of claim 42, wherein  
said first, second, third and fourth upper wires are alternated on two parallel rows such that ends of said first and second upper wires on one of the parallel rows oppose to ends of said third and fourth upper wires on the other of the parallel rows.

#### REMARKS

In the Final Office Action, the Examiner objected to the drawings under 37 C.F.R. § 1.83(a); rejected claims 1, 2, 5-23, 31, 32, 34, 40, and 42 under 35 U.S.C. § 112, first paragraph; rejected claims 36, 37, 38-40, and 44 under 35 U.S.C. § 112, second paragraph; and rejected claim 33 under 35 U.S.C. § 102(e) as anticipated by Huang et al. (U.S. Patent No. 6,162,686, hereinafter "Huang").